

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

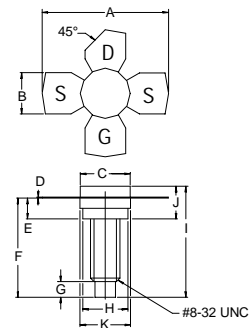
The **ASI BLV30** is Designed for Television Band IV & V Applications up to 860 MHz.

**FEATURES:**

- Common Emitter
- $P_G = 10$  dB at 2.0 W/860 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	1.5 A
$V_{CBO}$	60 V
$V_{CEO}$	30 V
$V_{EBO}$	4.0 V
$P_{DISS}$	15.9 W @ $T_C = 25^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
$\theta_{JC}$	$10^\circ\text{C/W}$

**PACKAGE STYLE .280 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 10$ mA	60			V
$BV_{CEO}$	$I_C = 50$ mA	30			V
$BV_{EBO}$	$I_E = 4.0$ mA	4.0			V
$I_{CBO}$	$V_{CB} = 30$ V			4.0	mA
$h_{FE}$	$V_{CE} = 25$ V $I_C = 500$ mA	15		120	---
$C_{OB}$	$V_{CB} = 28$ V $f = 1.0$ MHz			10	pF
$P_G$	$V_{CE} = 25$ V $I_C = 410$ mA $f = 860$ MHz	10			dB
$IMD_1$	$P_{OUT} = 2.0$ W	-60			dBc